

HIGH VOLTAGE NPN MULTIEPITAXIAL FAST-SWITCHING TRANSISTOR

- HIGH VOLTAGE CAPABILITY
- VERY HIGH SWITCHING SPEED
- LOW BASE-DRIVE REQUIREMENTS

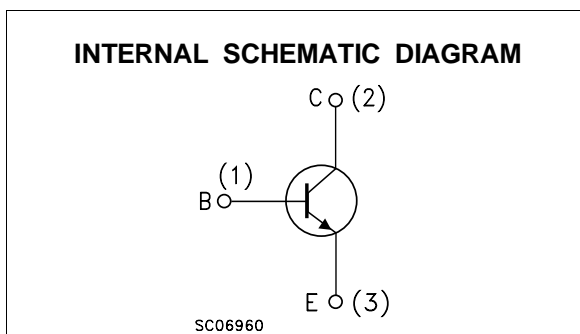
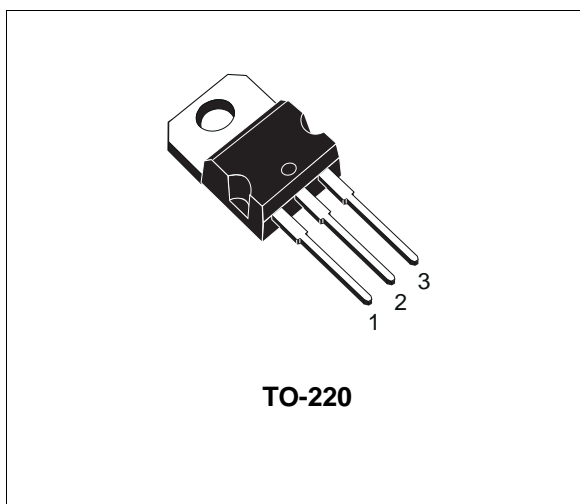
APPLICATIONS

- ELECTRONIC BALLASTS FOR FLUORESCENT LIGHTING
- SWITCH MODE POWER SUPPLIES

DESCRIPTION

The BU505 is a high voltage NPN fastswitching transistor designed to be used in lighting application, like electronic ballas for fluorescent lamps.

Its characteristics make it also ideal for power supplies.



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CES}	Collector-Emitter Voltage ($V_{BE} = 0$)	1500	V
V_{CEO}	Collector-Emitter Voltage ($I_B = 0$)	700	V
I_C	Collector Current	2.5	A
I_{CM}	Collector Peak Current ($t_p < 5$ ms)	4	A
I_B	Base Current	1	A
I_{BM}	Base Peak Current ($t_p < 5$ ms)	2	A
P_{tot}	Total Dissipation at $T_c \leq 25$ °C	75	W
T_{stg}	Storage Temperature	-65 to 150	°C
T_j	Max. Operating Junction Temperature	150	°C

BU505

THERMAL DATA

$R_{thj-case}$	Thermal Resistance Junction-case	Max	1.67	$^{\circ}C/W$
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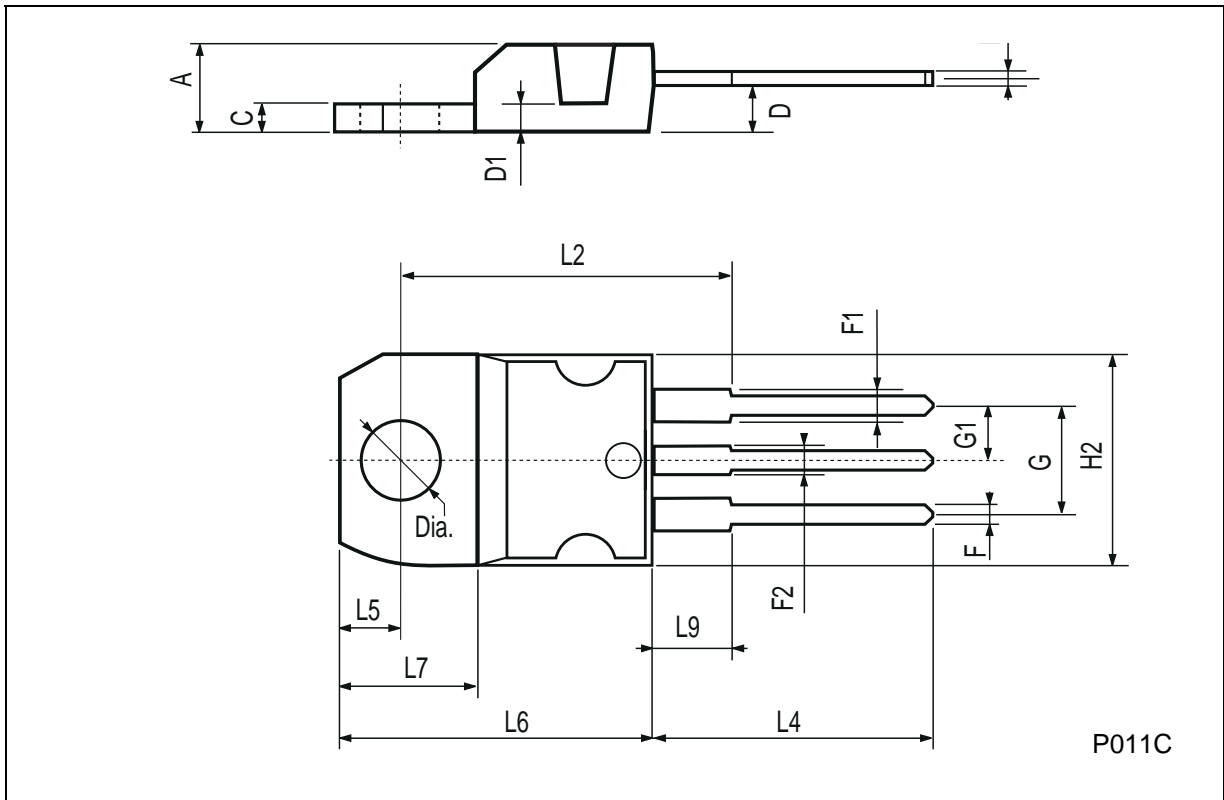
ELECTRICAL CHARACTERISTICS ($T_{case} = 25^{\circ}C$ unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{CES}	Collector Cut-off Current ($V_{BE} = 0$)	$V_{CE} = V_{CES}$ $V_{CE} = V_{CES}$ $T_{case} = 125^{\circ}C$			0.15 1	mA mA
I_{EBO}	Emitter Cut-off Current ($I_C = 0$)	$V_{EB} = 5 V$			1	mA
$V_{CEO(sus)}$	Collector-emitter Sustaining Voltage	$I_C = 100 mA$ $L = 25mH$	700			V
$V_{CE(sat)*}$	Collector-emitter Saturation Voltage	$I_C = 2 A$ $I_B = 0.9 A$			5	V
$V_{BE(sat)*}$	Base-emitter Saturation Voltage	$I_C = 2 A$ $I_B = 0.9 A$			1.3	V
$I_{s/b}$	Second Breakdown Current	$V_{CE} = 120 V$ $t = 200 \mu s$	2			A
t_s	Storage Time	$V_{Clamp} = 250V$ $I_C = 2 A$ $I_{B1} = 0.7 A$ $V_{be(off)} = -5V$ $R_{bb} = 0$ $L = 200\mu H$		2 350		μs ns

* Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %.

TO-220 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
C	1.23		1.32	0.048		0.051
D	2.40		2.72	0.094		0.107
D1		1.27			0.050	
E	0.49		0.70	0.019		0.027
F	0.61		0.88	0.024		0.034
F1	1.14		1.70	0.044		0.067
F2	1.14		1.70	0.044		0.067
G	4.95		5.15	0.194		0.203
G1	2.4		2.7	0.094		0.106
H2	10.0		10.40	0.393		0.409
L2		16.4			0.645	
L4	13.0		14.0	0.511		0.551
L5	2.65		2.95	0.104		0.116
L6	15.25		15.75	0.600		0.620
L7	6.2		6.6	0.244		0.260
L9	3.5		3.93	0.137		0.154
DIA.	3.75		3.85	0.147		0.151



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